

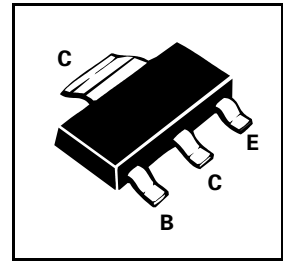
# SOT223 PNP SILICON PLANAR MEDIUM POWER TRANSISTOR

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## FZT549

PARTMARKING DETAIL – FZT549



### ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CBO}$	-35	V
Collector-Emitter Voltage	$V_{CEO}$	-30	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Peak Pulse Current	$I_{CM}$	-2	A
Continuous Collector Current	$I_C$	-1	A
Power Dissipation at $T_{amb}=25^{\circ}C$	$P_{tot}$	2	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

### ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ ).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-35			V	$I_C = -100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-30			V	$I_C = -10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E = -100\mu A$
Collector Cut-Off Current	$I_{CBO}$			-0.1 -10	$\mu A$ $\mu A$	$V_{CB} = -30V$ $V_{CB} = -30V, T_{amb} = 100^{\circ}C$
Emitter Cut-Off Current	$I_{EBO}$			-0.1	$\mu A$	$V_{EB} = -4V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.50 -0.75	V V	$I_C = -1A, I_B = -100mA^*$ $I_C = -2A, I_B = -200mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-1.25	V	$I_C = -1A, I_B = -100mA^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$			-1.0	V	$I_C = -1A, V_{CE} = -2V^*$
Static Forward Current	$h_{FE}$	70 100 80 30		300		$I_C = -50mA, V_{CE} = -2V$ $I_C = -500mA, V_{CE} = -2V^*$ $I_C = -1A, V_{CE} = -2V^*$ $I_C = -2A, V_{CE} = -2V^*$
Transition Frequency	$f_T$	100			MHz	$I_C = -100mA, V_{CE} = -5V,$ $f = 100MHz$
Output Capacitance	$C_{obo}$			10	pF	$V_{CB} = -10V, f = 1MHz$

\*Measured under pulsed conditions. Pulse width=300 $\mu s$ . Duty cycle  $\leq 2\%$

For typical characteristics graphs see FMMT549 datasheet.